

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number		10581940
	Filing Date		2006-06-07
	First Named Inventor	Tetsuo Fujii et al.	
	Art Unit	2815	
	Examiner Name	Jerome Jackson Jr.	
	Attorney Docket Number	30794.108-US-WO	

U.S.PATENTS						Remove
Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear
	1	3739217		1973-06-12	Bergh et al.	
	2	5773369		1998-06-30	Hu et al.	
	3	5779924		1998-07-14	Krames et al.	
	4	6277665		2001-08-21	Ma et al.	
	5	6441403		2002-08-27	Chang et al.	
	6	6657236		2003-12-02	Thibeault et al.	
	7	6847057		2005-01-25	Gardner et al.	
	8	7135709		2006-11-14	Wirth et al.	

If you wish to add additional U.S. Patent citation information please click the Add button.

Add

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number		10581940
	Filing Date		2006-06-07
	First Named Inventor	Tetsuo Fujii et al.	
	Art Unit	2815	
	Examiner Name	Jerome Jackson Jr.	
	Attorney Docket Number	30794.108-US-WO	

U.S.PATENT APPLICATION PUBLICATIONS							Remove
Examiner Initial*	Cite No	Publication Number	Kind Code ¹	Publication Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear	
	1	20030057444		2003-03-27	Niki et al.		
	2	20030178626		2003-09-25	Sugiyama et al.		

If you wish to add additional U.S. Published Application citation information please click the Add button. Add

FOREIGN PATENT DOCUMENTS								Remove
Examiner Initial*	Cite No	Foreign Document Number ³	Country Code ²	Kind Code ⁴	Publication Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear	T ⁵
	1							<input type="checkbox"/>

If you wish to add additional Foreign Patent Document citation information please click the Add button. Add

NON-PATENT LITERATURE DOCUMENTS				Remove
Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published.	T5	
	1	DOROGAN et al., "Photoelectrochemical etching of GaN-AlGaIn heterostructures formed on sapphire substrates," Moldavian Journal of the Physical Sciences, N2, 2002, pp. 156-159.	<input type="checkbox"/>	
	2	FUJII et al., "Increase in the extraction efficiency of GaN-based light-emitting diodes via surface roughening," Applied Physics Letters, vol. 84, no. 6, 9 February 2004, pp. 855-857.	<input type="checkbox"/>	
	3	HWANG et al., "Efficient wet etching of GaN and p-GaN assisted with chopped UV source," Superlattices and Microstructures 35, 2004, pp. 45-57.	<input type="checkbox"/>	

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Not for submission under 37 CFR 1.99)

Application Number	10581940
Filing Date	2006-06-07
First Named Inventor	Tetsuo Fujii et al.
Art Unit	2815
Examiner Name	Jerome Jackson Jr.
Attorney Docket Number	30794.108-US-WO

4	SCHNITZER et al., "30% external quantum efficiency from surface textured, thin-film light-emitting diodes," Appl. Phys. Lett. 63 (16), 18 October 1993, pp. 2174-2176.	<input type="checkbox"/>
5	YAMADA et al., "InGaN-based near-ultraviolet and blue-light-emitting diodes with high external quantum efficiency using a patterned sapphire substrate and a mesh electrode," Jpn. J. Appl. Phys., vol. 41, 2002, pp. L1431-L1433.	<input type="checkbox"/>
6	QI et al., "Study on the formation of dodecagonal pyramid on nitrogen polar GaN surface etched by hot H3PO4," Applied Physics Letters, 95, 2009, pp. 071114-1-071114-3.	<input type="checkbox"/>
7	SHCHEKIN et al., "High performance thin-film flip-chip InGaN-GaN light-emitting diodes," Applied Physics Letters 89, 2006, 071109-1-071109-3.	<input type="checkbox"/>
8	HARLE et al., "Advanced technologies for high efficiency GaInN LEDs for solid state lighting," Third International Conference on Solid State Lighting, Proceedings of the SPIE, vol. 5187, 2004, pp. 34-40 (English Abstract only).	<input type="checkbox"/>

If you wish to add additional non-patent literature document citation information please click the Add button

EXAMINER SIGNATURE

Examiner Signature		Date Considered	
--------------------	--	-----------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through a citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ See Kind Codes of USPTO Patent Documents at www.USPTO.GOV or MPEP 901.04. ² Enter office that issued the document, by the two-letter code (WIPO Standard ST.3). ³ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁴ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁵ Applicant is to place a check mark here if English language translation is attached.